

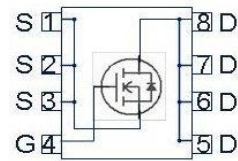
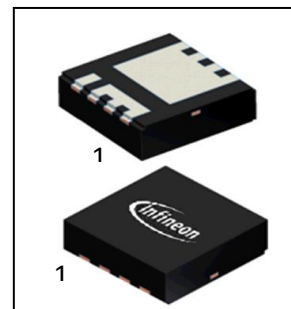
OptiMOS™ -5 Power-Transistor

Product Summary

V_{DS}	100	V
$R_{DS(on),max}$	24	mΩ
I_D	30	A

Features

- OptiMOS™ - power MOSFET for automotive applications
- N-channel - Enhancement mode - Logic Level
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested
- Feasible for automatic optical inspection (AOI)

PG-TSDSON-8


Type	Package	Marking
IAUZ30N10S5L240	PG-TSDSON-8	5N1L240

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}$, $V_{GS}=10\text{V}$	30	A
		$T_C=100\text{ °C}$, $V_{GS}=10\text{V}^{1)}$	22	
Pulsed drain current ¹⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	120	
Avalanche energy, single pulse ¹⁾	E_{AS}	$I_D=12\text{A}$	17	mJ
Avalanche current, single pulse	I_{AS}	-	12	A
Gate source voltage	V_{GS}	-	±20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$ $T_J=175\text{ °C}$	45.5	W
Operating and storage temperature	T_j , T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	-

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics¹⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	3.3	K/W
Thermal resistance, junction - ambient	R_{thJA}	6 cm ² cooling area ²⁾	-	-	62	

Electrical characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=15\mu A$	1.2	1.7	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	-	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_j=125^\circ\text{C}^{1)}$	-	-	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=15A$	-	26	31	$m\Omega$
		$V_{GS}=10V, I_D=15A$	-	19.5	24	
Gate resistance ¹⁾	R_G		-	1.5	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics¹⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$	-	640	832	pF
Output capacitance	C_{oss}		-	113	147	
Reverse transfer capacitance	C_{rss}		-	7.9	11.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50V, V_{GS}=10V,$ $I_D=30A, R_G=3.5\Omega$	-	2	-	ns
Rise time	t_r		-	1	-	
Turn-off delay time	$t_{d(off)}$		-	4.6	-	
Fall time	t_f		-	3.4	-	

Gate Charge Characteristics¹⁾

Gate to source charge	Q_{gs}	$V_{DD}=50V, I_D=15A,$ $V_{GS}=0 \text{ to } 10V$	-	2.1	2.7	nC
Gate to drain charge	Q_{gd}		-	1.9	2.9	
Gate charge total	Q_g		-	9.5	14	
Gate plateau voltage	$V_{plateau}$		-	3.3	-	V

Reverse Diode

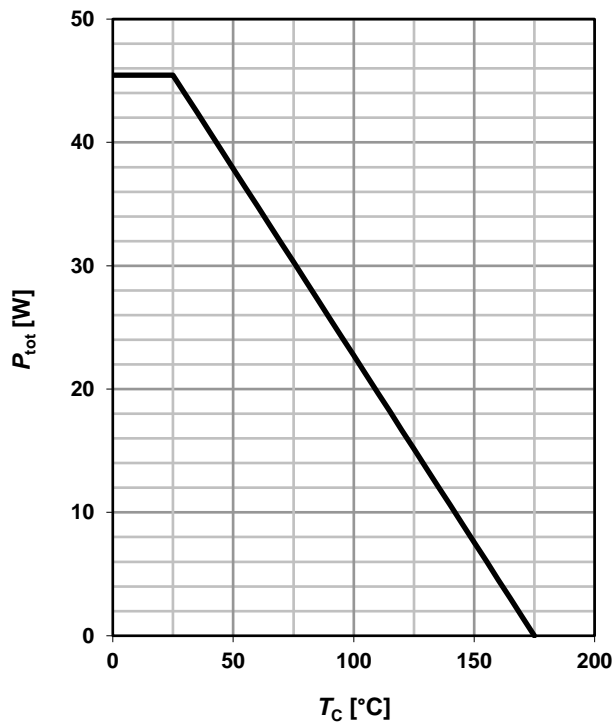
Diode continuous forward current ¹⁾	I_S	$T_C=25^\circ C$	-	-	30	A
Diode pulse current ¹⁾	$I_{S,pulse}$		-	-	120	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=15A,$ $T_j=25^\circ C$	-	0.9	1.1	V
Reverse recovery time ¹⁾	t_{rr}	$V_R=50V, I_F=30A,$ $di_F/dt=100A/\mu s$	-	37	-	ns
Reverse recovery charge ¹⁾	Q_{rr}		-	34	-	nC

¹⁾ Specified by design. Not subject to production test.

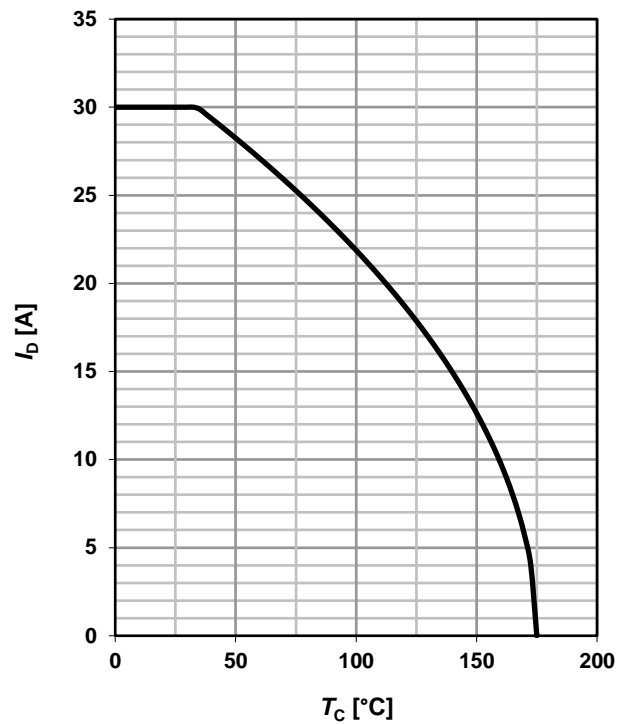
²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

1 Power dissipation

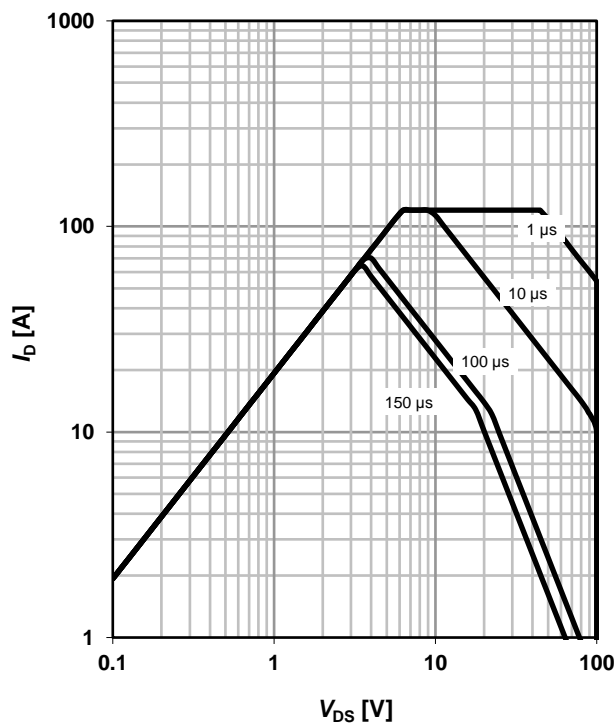
$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$


2 Drain current

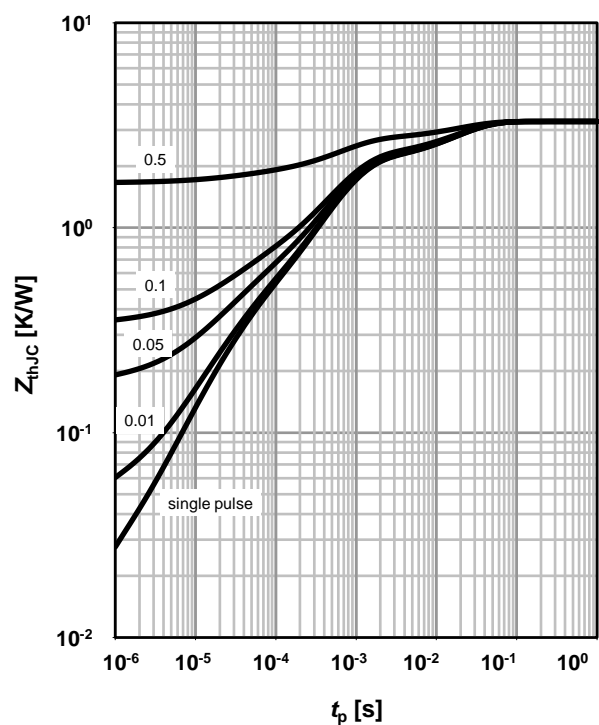
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$


3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

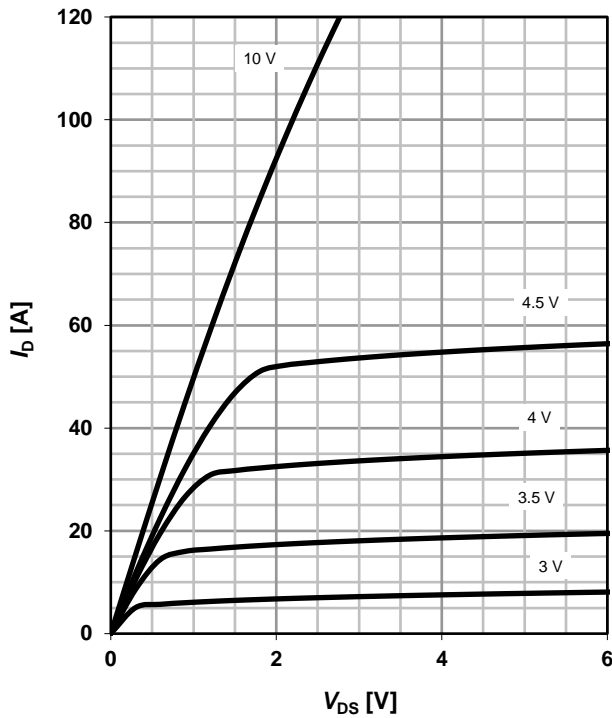
 parameter: t_p

4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

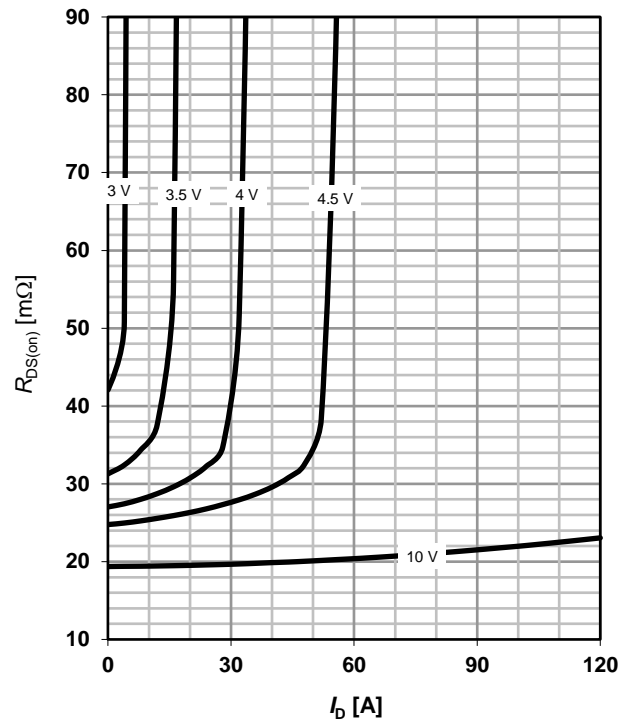
 parameter: $D = t_p/T$


5 Typ. output characteristics

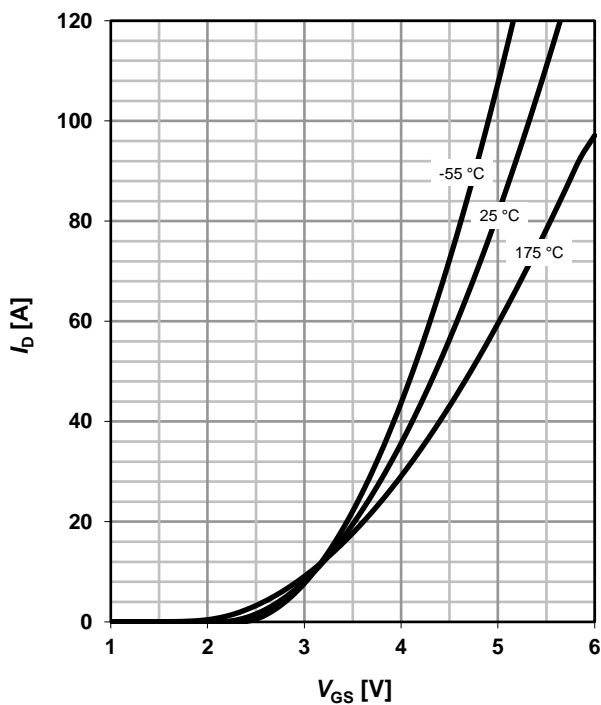
$$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

6 Typ. drain-source on-state resistance

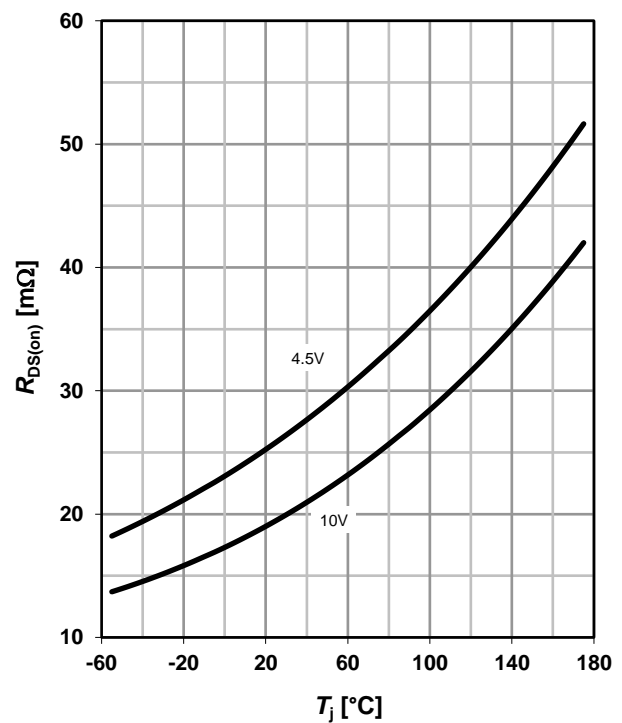
$$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} = 6V$$

 parameter: T_j

8 Typ. drain-source on-state resistance

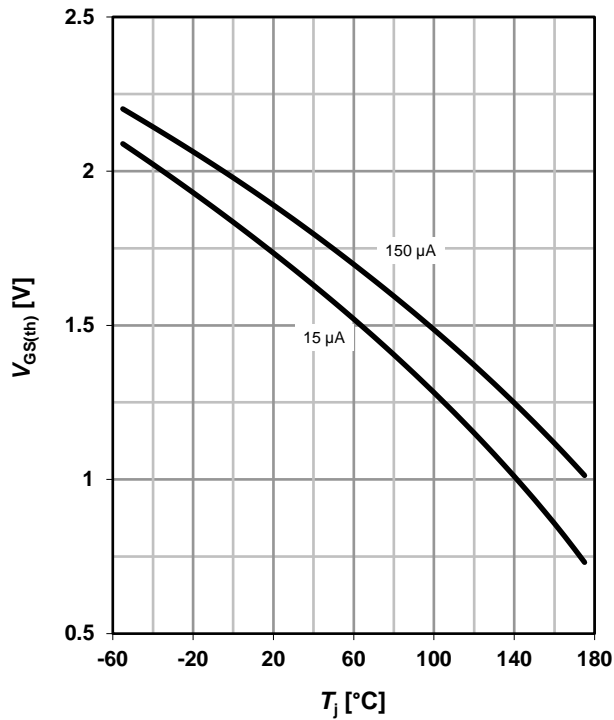
$$R_{DS(on)} = f(T_j); I_D = 15A$$

 parameter: V_{GS}


9 Typ. gate threshold voltage

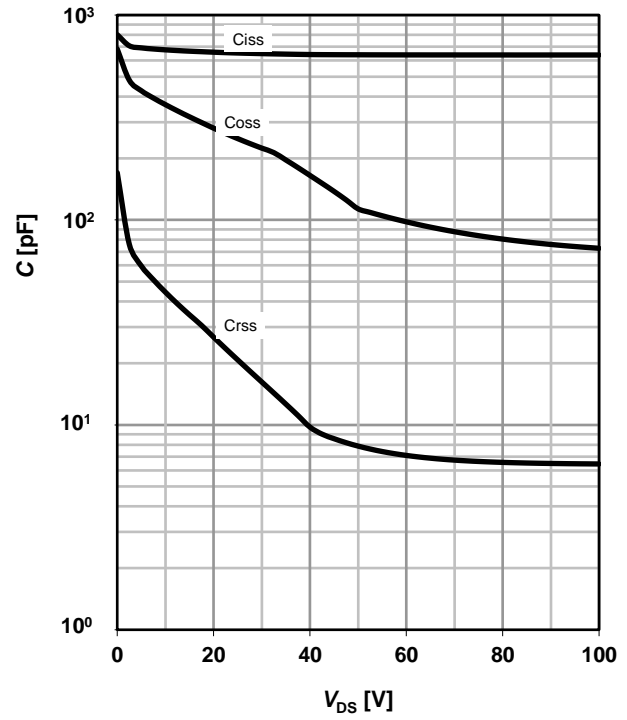
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

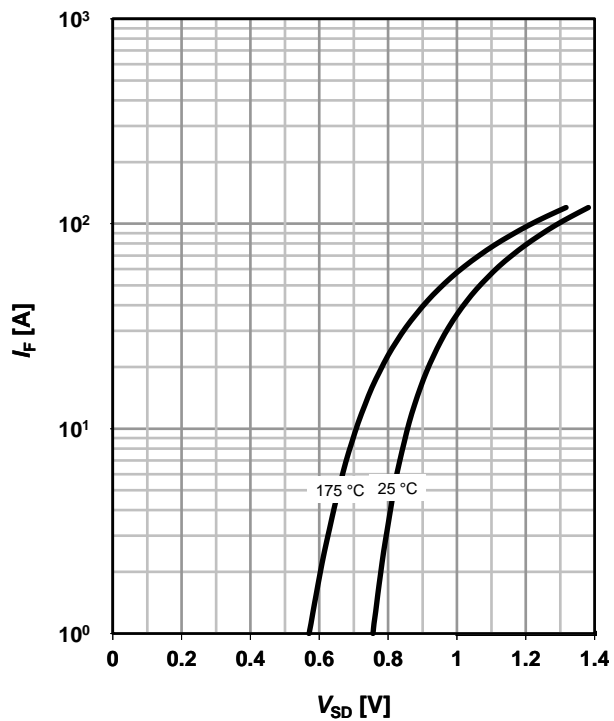
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



11 Typical forward diode characteristics

$I_F = f(V_{SD})$

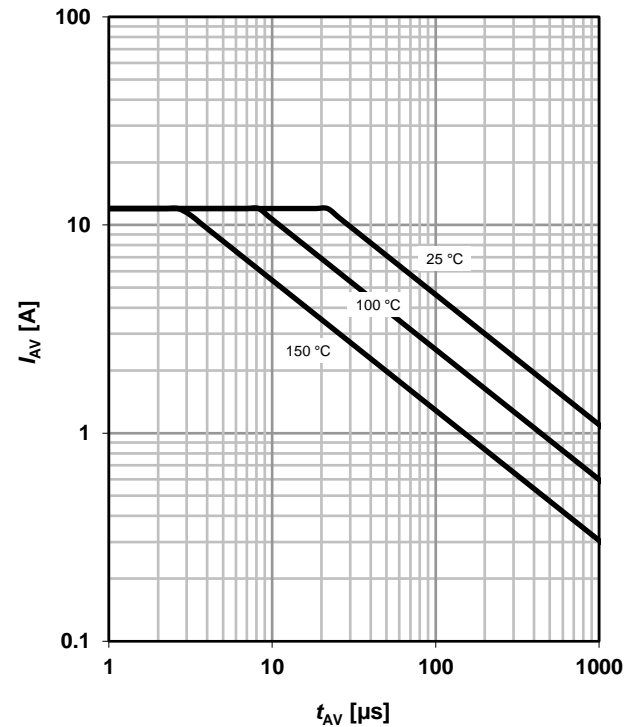
parameter: T_j



12 Avalanche characteristics

$I_{AS} = f(t_{AV})$

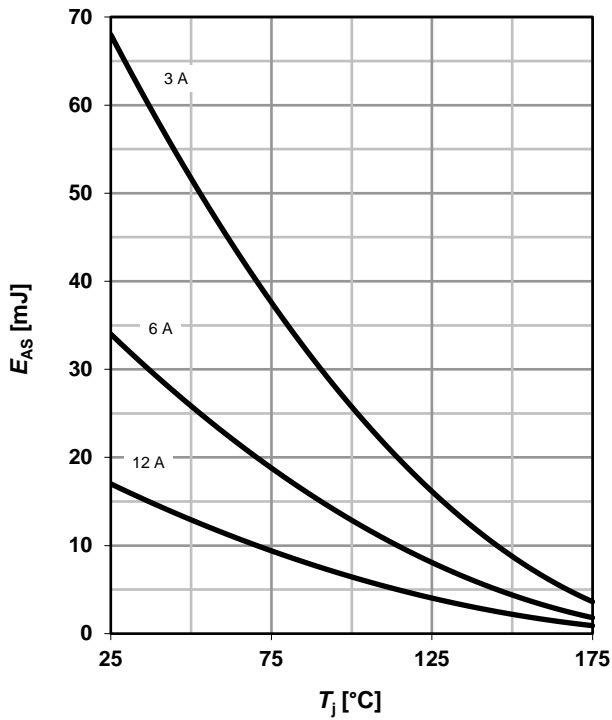
parameter: $T_{j(start)}$



13 Avalanche energy

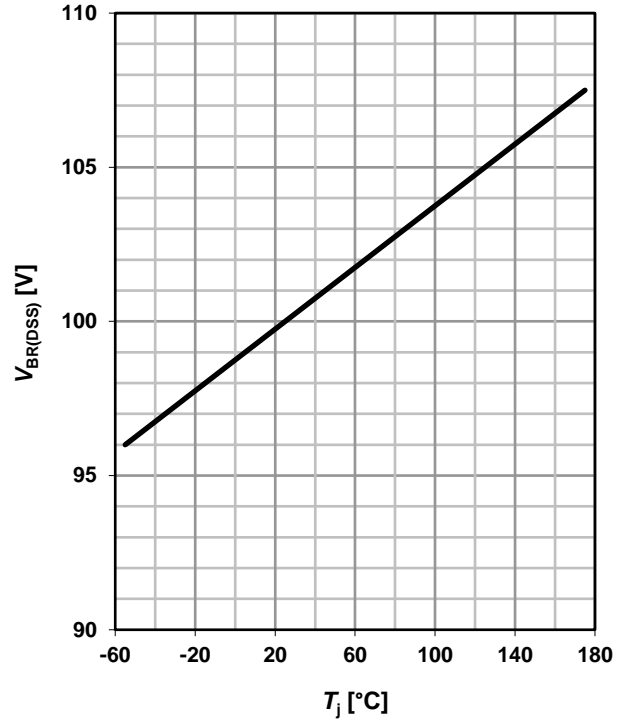
$$E_{AS} = f(T_j)$$

parameter: I_D



14 Drain-source breakdown voltage

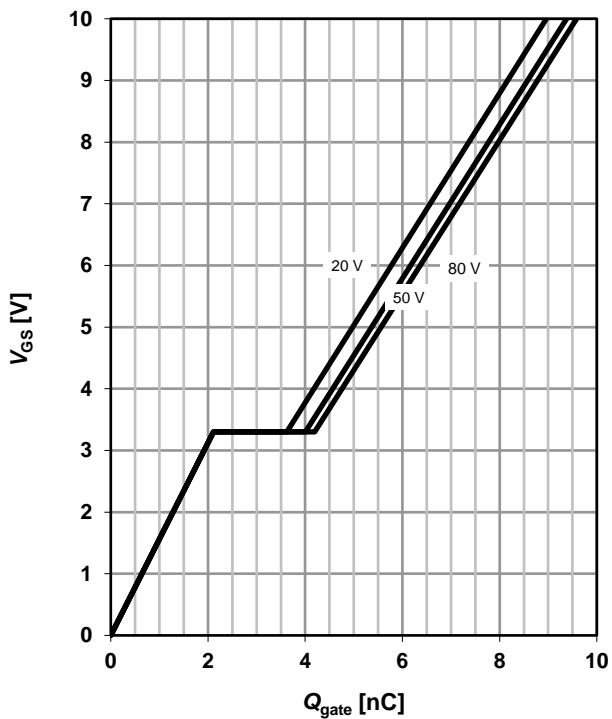
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



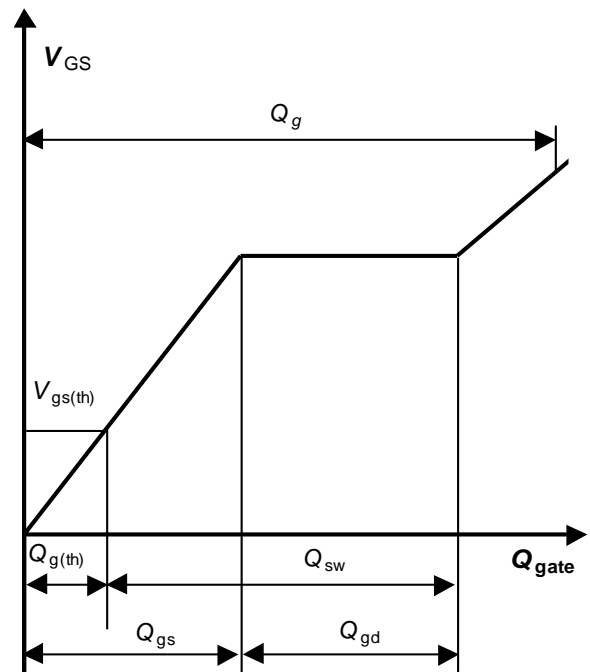
15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 15 \text{ A pulsed}$$

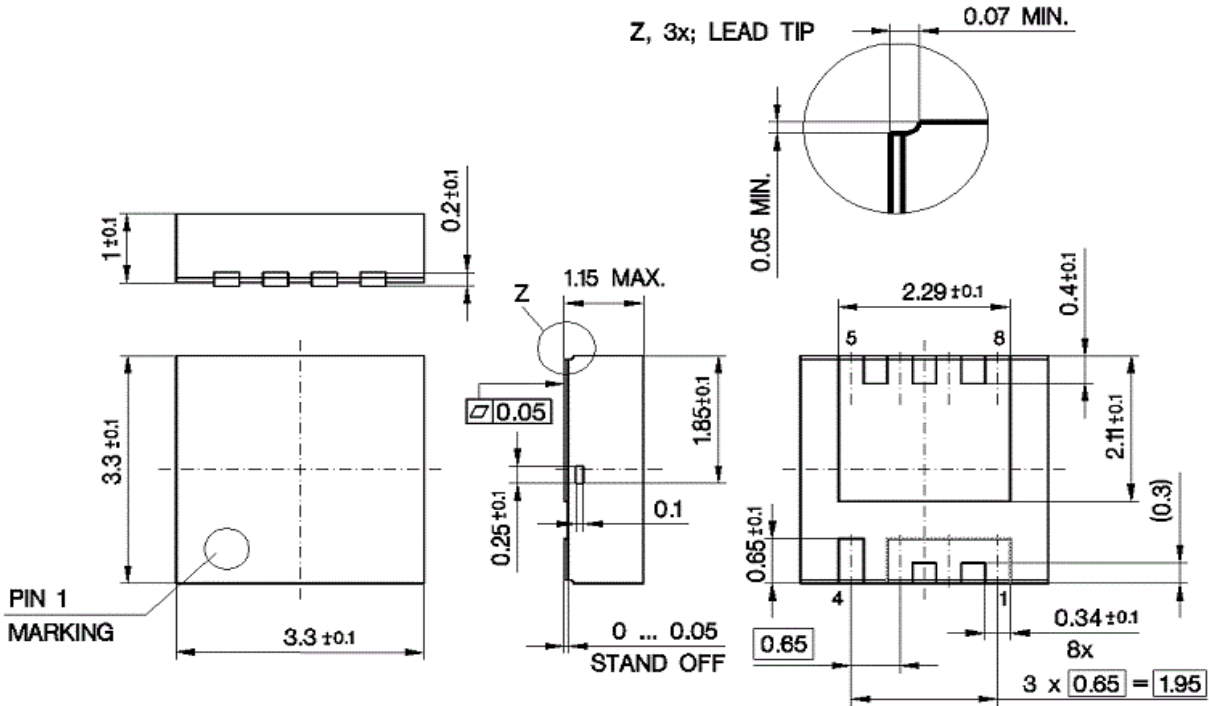
parameter: V_{DD}



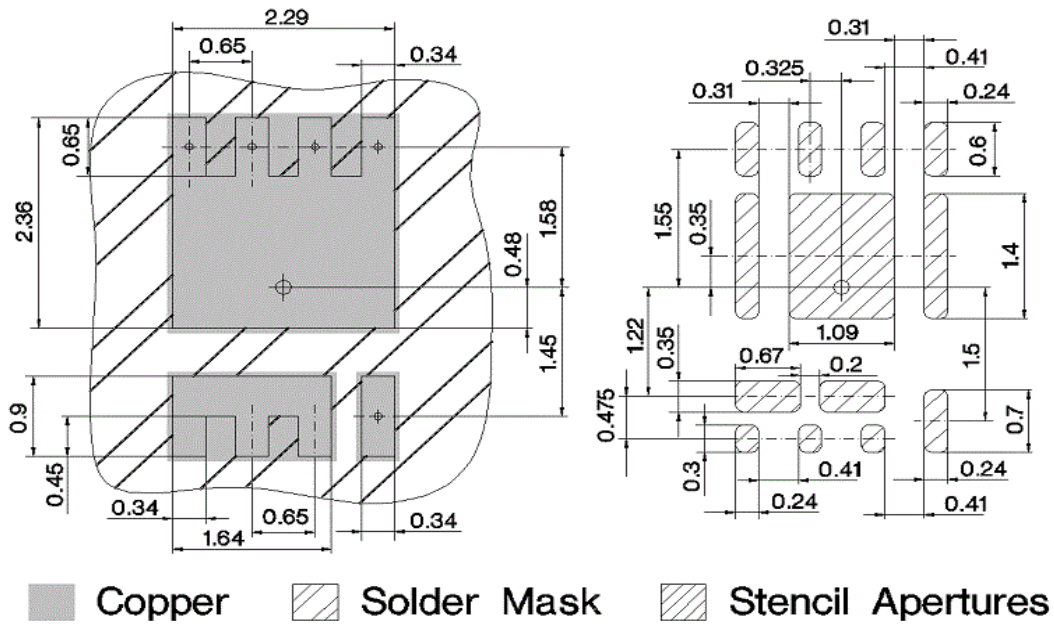
16 Gate charge waveforms



PG-TSDSON-8: Outline

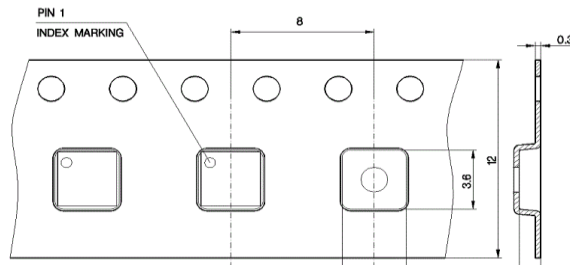


Footprint



Dimensions in mm

Packaging



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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Revision 1.0	23.07.2019	Final Data Sheet

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon\(英飞凌\)](#)